

Shin Mou

List of Publications by Year in descending order

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Version: 2024-02-01

22
papers

1,454
citations

567281

15
h-index

713466

21
g-index

22
all docs

22
docs citations

22
times ranked

1054
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | $\hat{\Gamma}^2$ -Gallium oxide power electronics. APL Materials, 2022, 10, . | 5.1 | 184 |
| 2 | Si doping in MOCVD grown (010) $\hat{\Gamma}^2$ -(Al _x Ga _{1-x}) ₂ O ₃ thin films. Journal of Applied Physics, 2022, 131, . | 2.5 | 15 |
| 3 | Adsorption-controlled growth of Ga ₂ O ₃ by suboxide molecular-beam epitaxy. APL Materials, 2021, 9, . | 5.1 | 38 |
| 4 | $\hat{\Gamma}^3$ -phase inclusions as common structural defects in alloyed $\hat{\Gamma}^2$ -(Al _x Ga _{1-x}) ₂ O ₃ and doped $\hat{\Gamma}^2$ -Ga ₂ O ₃ films. APL Materials, 2021, 9, . | 5.1 | 23 |
| 5 | Lateral $\hat{\Gamma}^2$ -Ga ₂ O ₃ field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002. | 2.0 | 85 |
| 6 | Toward high voltage radio frequency devices in $\hat{\Gamma}^2$ -Ga ₂ O ₃ . Applied Physics Letters, 2020, 117, . | 3.3 | 23 |
| 7 | Pulsed Power Performance of $\hat{\Gamma}^2$ -Ga ₂ O ₃ MOSFETs at L-Band. IEEE Electron Device Letters, 2020, 41, 989-992. | 3.9 | 32 |
| 8 | Reduction of unintentional Si doping in $\hat{\Gamma}^2$ -Ga ₂ O ₃ grown via plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 043403. | 2.1 | 20 |
| 9 | Tailoring the Potential Landscape and Electrical Properties of 2D MoS ₂ using Gold Nanostructures of Different Coverage Density. Journal of Physical Chemistry C, 2020, 124, 6461-6466. | 3.1 | 3 |
| 10 | MOCVD growth of high purity Ga ₂ O ₃ epitaxial films using trimethylgallium precursor. Applied Physics Letters, 2020, 117, . | 3.3 | 77 |
| 11 | Electrical Properties 1. Springer Series in Materials Science, 2020, , 389-405. | 0.6 | 0 |
| 12 | Edge Doping Effect to the Surface Plasmon Resonances in Graphene Nanoribbons. Journal of Physical Chemistry C, 2019, 123, 19820-19827. | 3.1 | 8 |
| 13 | Study of defects in $\hat{\Gamma}^2$ -Ga ₂ O ₃ by isothermal capacitance transient spectroscopy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2019, 37, 041204. | 1.2 | 3 |
| 14 | Zeeman spin-splitting in the (010) $\hat{\Gamma}^2$ -Ga ₂ O ₃ two-dimensional electron gas. Applied Physics Letters, 2019, 115, . | 3.3 | 1 |
| 15 | Demonstration of high mobility and quantum transport in modulation-doped $\hat{\Gamma}^2$ -(Al _x Ga _{1-x}) ₂ O ₃ /Ga ₂ O ₃ heterostructures. Applied Physics Letters, 2018, 112, . | 3.3 | 264 |
| 16 | Towards High-Mobility Heteroepitaxial $\hat{\Gamma}^2$ -Ga ₂ O ₃ on Sapphire - Dependence on The Substrate Off-Axis Angle. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700467. | 1.8 | 84 |
| 17 | $\hat{\Gamma}^2$ -Ga ₂ O ₃ defect study by steady-state capacitance spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 091101. | 1.5 | 17 |
| 18 | Microwave imaging of etching-induced surface impedance modulation of graphene monolayer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, 05G508. | 2.1 | 3 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Donors and deep acceptors in $\hat{\text{I}}^2\text{-Ga}_2\text{O}_3$. Applied Physics Letters, 2018, 113, . | 3.3 | 203 |
| 20 | Ge-Doped $\{\eta\}$ -Ga ₂ O ₃ MOSFETs. IEEE Electron Device Letters, 2017, 38, 775-778. | 3.9 | 165 |
| 21 | Incomplete Ionization of a 110 $\hat{\text{a}}\%$ meV Unintentional Donor in $\hat{\text{I}}^2\text{-Ga}_2\text{O}_3$ and its Effect on Power Devices. Scientific Reports, 2017, 7, 13218. | 3.3 | 84 |
| 22 | Heteroepitaxy of N-type $\hat{\text{I}}^2\text{-Ga}_2\text{O}_3$ thin films on sapphire substrate by low pressure chemical vapor deposition. Applied Physics Letters, 2016, 109, . | 3.3 | 122 |